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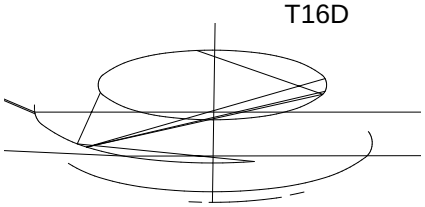
T16D



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KK4000/25	2500	2500	2500
KK4000/28	2800	2800	2800

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 180 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	V_D=12V;R_L=3ohms;T_j=+25ºC
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_D=12V;R_L=3ohms;T_j=+25ºC
Peak negative voltage	V_{GRM}		5		V